

Technical Data Data Sheet N1174, Rev. A **Green Products**

183NQ080-1 183NQ100-1 SCHOTTKY RECTIFIER

Applications:

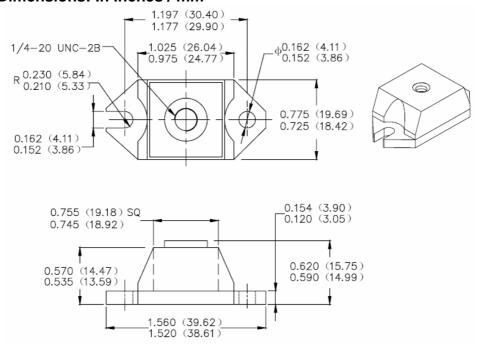
• Switching power supply • Converters • Free-Wheeling diodes • Reverse battery protection

Features:

- 175℃ T_J operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5'S
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Very low forward voltage drop
- · High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request



Mechanical Dimensions: In Inches / mm



PRM1-1(HALF PAK Module)

MARKING, MOLDING RESIN

Marking for183NQ080-1, 1st row SS YYWWL, 2nd row 183NQ080-1 Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number Molding resin

Epoxy resin UL:94V-0

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Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Inverse Voltage	V_{RWM}	-	80 183NQ080-1		V
			100	183NQ100-1	
Max. Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =116℃, rectangular wave form	180		А
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	1860		А
Non-Repetitive Avalanche Energy	E _{AS}	T _J =25℃,I _{AS} =0.50A,L=60mH	15		mJ
Repetitive Avalanche Current	I _{AR}	Current decaying linearly to zero in 1 μ sec Frequency limited by T $_J$ max. V_A =1.5 \times V_R typical	1		А

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V _{F1}	 @ 180A, Pulse, T_J = 25 °C @ 360A, Pulse, T_J = 25 °C 	0.95 1.14	V
	V _{F2}	 @ 180A, Pulse, T_J = 125 °C @ 360A, Pulse, T_J = 125 °C 	0.75 0.89	V
Max. Reverse Current (per	I _{R1}	$@V_R = \text{rated } V_R T_J = 25 ^{\circ}\text{C}$	4.5	mA
leg) *	I _{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	60	mA
Max. Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	4150	pF
Typical Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	6.0	nΗ
Max. Voltage Rate of Change	dv/dt	-	10,000	V/µs

[■] Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specific	Units			
Max. Junction Temperature	TJ	-	-55 to -	°C			
Max. Storage Temperature	T _{stg}	-	-55 to +175		°C		
Maximum Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.30		°C/W		
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.15		°C/W		
Mounting Torque	Тм	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm		
Approximate Weight	wt	-	25.6		g		
Case Style	PRM1-1						

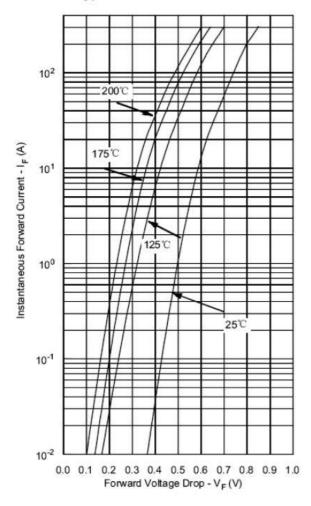
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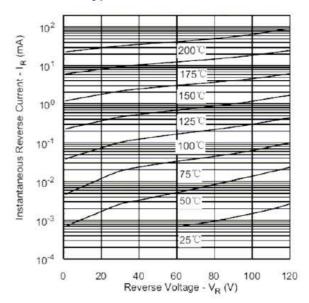


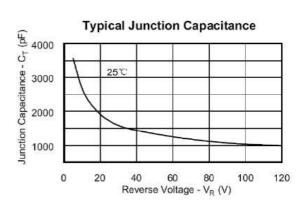
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Typical Forward Characteristics



Typical Reverse Characteristics





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183NQ...-1 SERIES

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